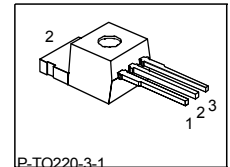


Cool MOS™ Power Transistor
Feature

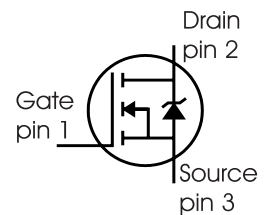
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁰⁾ for target applications

| | | |
|--------------|-----|----------|
| V_{DS} | 600 | V |
| $R_{DS(on)}$ | 1.4 | Ω |
| I_D | 3.2 | A |

PG-TO220



| Type | Package | Ordering Code | Marking |
|------------|----------|---------------|---------|
| SPP03N60S5 | PG-TO220 | Q67040-S4184 | 03N60S5 |


Maximum Ratings

| Parameter | Symbol | Value | Unit |
|----------------------------------------------------------------------------------------------------------------------------|---------------------|-------------|--------------------|
| Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$ | I_D | 3.2 2 | A |
| Pulsed drain current, t_p limited by T_{jmax} | $I_{D\text{ puls}}$ | 5.7 | |
| Avalanche energy, single pulse $I_D = 2.4\text{ A}$, $V_{DD} = 50\text{ V}$ | E_{AS} | 100 | mJ |
| Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ $I_D = 3.2\text{ A}$, $V_{DD} = 50\text{ V}$ | E_{AR} | 0.2 | |
| Avalanche current, repetitive t_{AR} limited by T_{jmax} | I_{AR} | 3.2 | A |
| Gate source voltage | V_{GS} | ± 20 | V |
| Gate source voltage AC ($f > 1\text{ Hz}$) | V_{GS} | ± 30 | |
| Power dissipation, $T_C = 25\text{ °C}$ | P_{tot} | 38 | W |
| Operating and storage temperature | T_j, T_{stg} | -55... +150 | $^{\circ}\text{C}$ |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---------------------------------------------------------------------------------------------------------------------|---------|-------|------|
| Drain Source voltage slope $V_{DS} = 480 \text{ V}$, $I_D = 3.2 \text{ A}$, $T_j = 125 \text{ }^\circ\text{C}$ | dv/dt | 20 | V/ns |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---------------------------------------------------------------------------------------------------|------------|--------|------|------|------|
| | | min. | typ. | max. | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3.3 | K/W |
| Thermal resistance, junction - ambient, leaded | R_{thJA} | - | - | 62 | |
| SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾ | R_{thJA} | - | - | 62 | |
| Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s ³⁾ | T_{sold} | - | - | 260 | °C |

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|---------------------------------------------|---------------|----------------------------------------------------------------------------------------------------|--------|------|------|---------------|
| | | | min. | typ. | max. | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$ | 600 | - | - | V |
| Drain-Source avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{V}$, $I_D=3.2\text{A}$ | - | 700 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=135\mu\text{A}$, $V_{GS}=V_{DS}$ | 3.5 | 4.5 | 5.5 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$ | - | 0.5 | 1 | μA |
| | | | - | - | 70 | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}$, $I_D=2\text{A}$, $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ | - | 1.26 | 1.4 | Ω |
| | | | - | 3.4 | - | |

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|------------------------------|--------------|----------------------------------------------------------------------------------------------|--------|------|------|------|
| | | | min. | typ. | max. | |
| Characteristics | | | | | | |
| Transconductance | g_{fs} | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 2\text{A}$ | - | 1.8 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | - | 420 | - | pF |
| Output capacitance | C_{oss} | | - | 150 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 3.6 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 350\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 3.2\text{A}$, $R_G = 20\Omega$ | - | 35 | | ns |
| Rise time | t_r | | - | 25 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 40 | | |
| Fall time | t_f | | - | 15 | 22.5 | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|-----------------|--------------------------------------------------------------------------------|---|------|----|----|
| Gate to source charge | Q_{gs} | $V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$ | - | 3.5 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 7 | - | |
| Gate charge total | Q_g | $V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$, $V_{GS} = 0$ to 10V | - | 12.4 | 16 | |
| Gate plateau voltage | $V_{(plateau)}$ | $V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$ | - | 8 | - | V |

⁰J-STD20 and JESD22

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

²Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

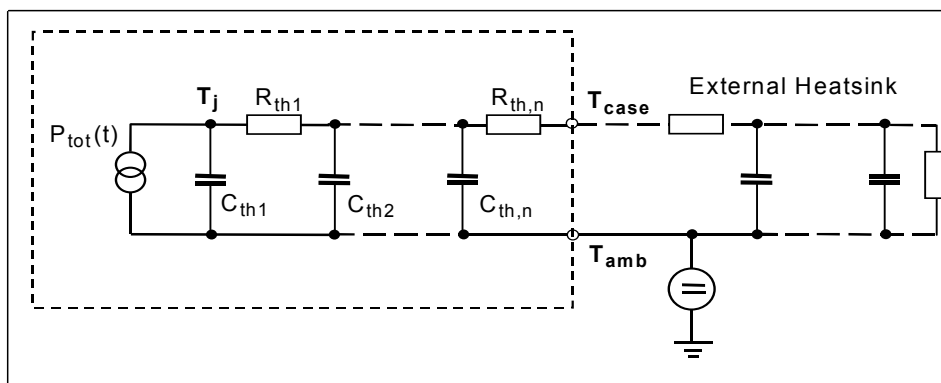
³Soldering temperature for TO-263: 220°C, reflow

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|------------------------------------------|----------|-----------------------------------|--------|------|------|---------------|
| | | | min. | typ. | max. | |
| Inverse diode continuous forward current | I_S | $T_C=25^\circ\text{C}$ | - | - | 3.2 | A |
| Inverse diode direct current, pulsed | I_{SM} | | - | - | 5.7 | |
| Inverse diode forward voltage | V_{SD} | $V_{GS}=0\text{V}, I_F=I_S$ | - | 1 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=350\text{V}, I_F=I_S,$ | - | 1000 | 1700 | ns |
| Reverse recovery charge | Q_{rr} | $di_F/dt=100\text{A}/\mu\text{s}$ | - | 2.3 | - | μC |

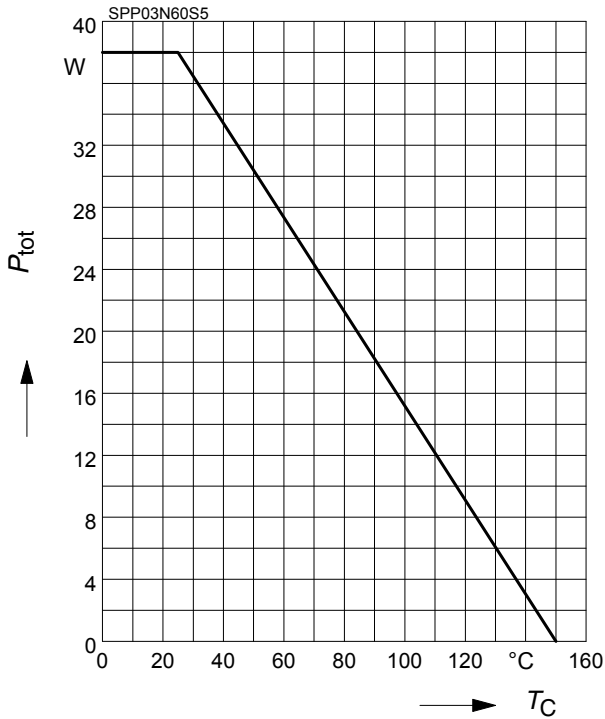
Typical Transient Thermal Characteristics

| Symbol | Value | Unit | Symbol | Value | Unit |
|--------------------|-------|------|---------------------|------------|------|
| | typ. | | | typ. | |
| Thermal resistance | | | Thermal capacitance | | |
| R_{th1} | 0.054 | K/W | C_{th1} | 0.00005232 | Ws/K |
| R_{th2} | 0.103 | | C_{th2} | 0.0002034 | |
| R_{th3} | 0.178 | | C_{th3} | 0.0002963 | |
| R_{th4} | 0.757 | | C_{th4} | 0.0009103 | |
| R_{th5} | 0.682 | | C_{th5} | 0.002084 | |
| R_{th6} | 0.202 | | C_{th6} | 0.024 | |



1 Power dissipation

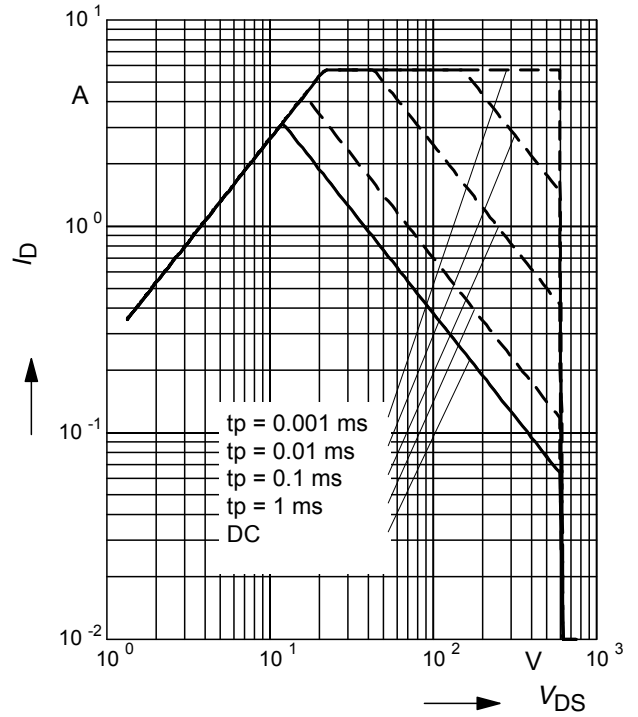
$$P_{tot} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

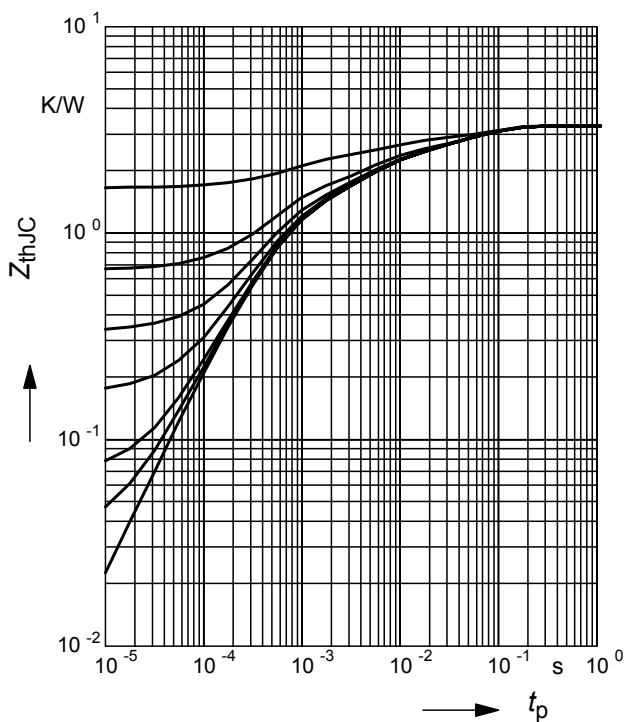
parameter : $D = 0$, $T_C = 25^\circ C$



3 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

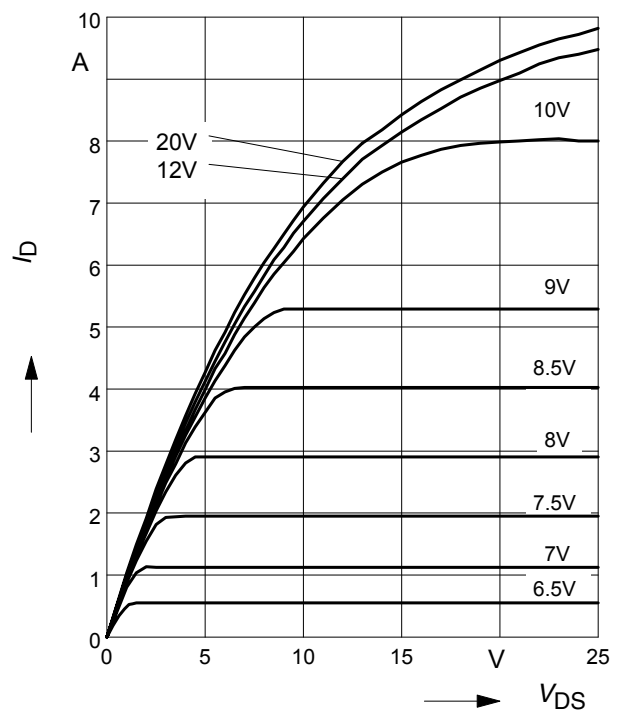
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ C$$

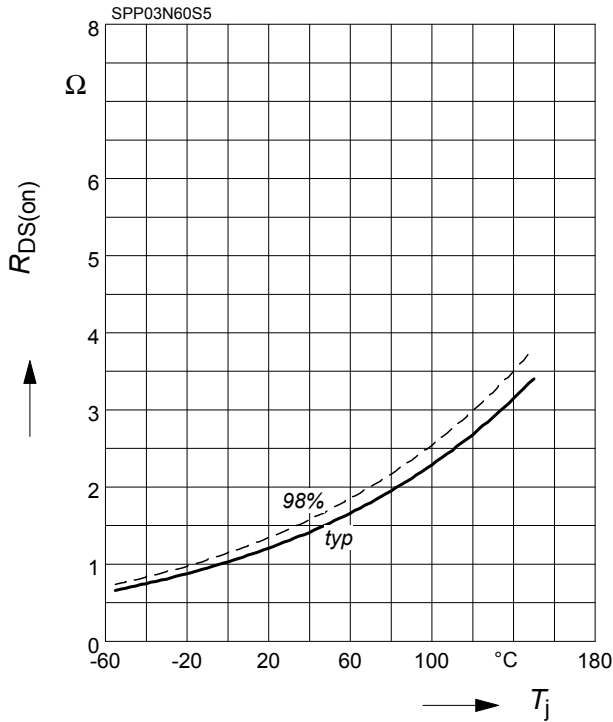
parameter: $t_p = 10 \mu s$, V_{GS}



5 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

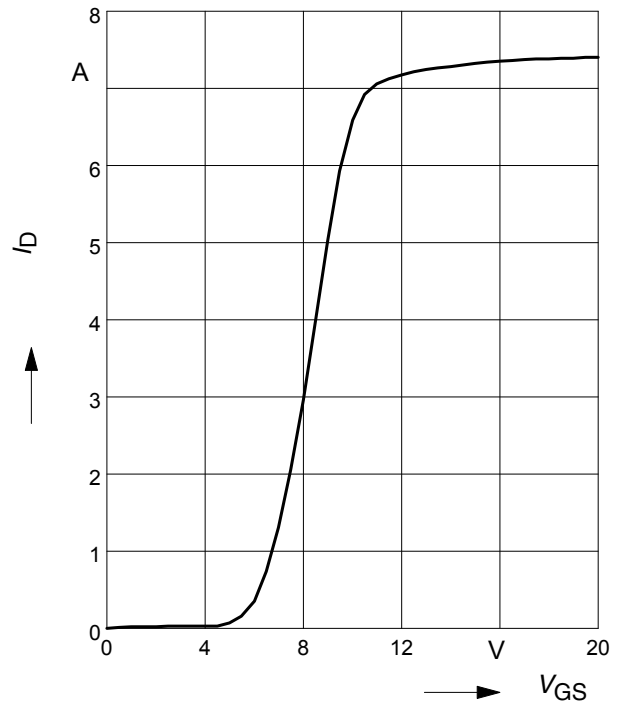
parameter: $I_D = 2 \text{ A}$, $V_{GS} = 10 \text{ V}$



6 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

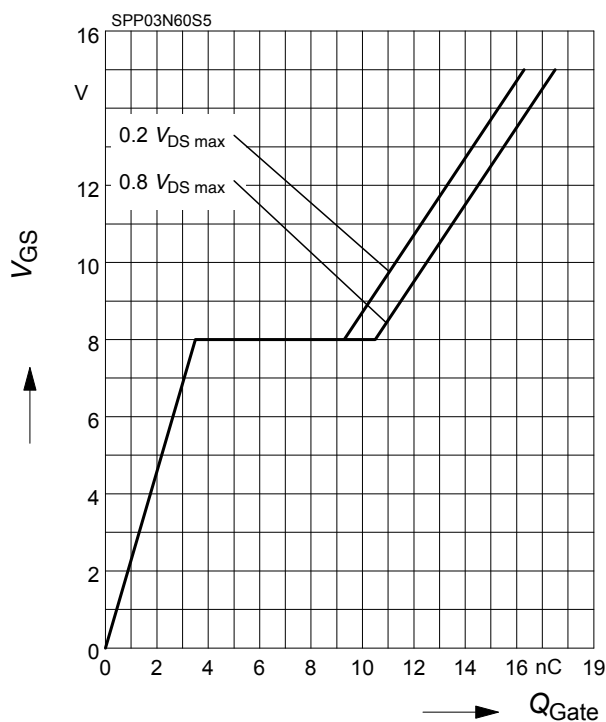
parameter: $t_p = 10 \mu\text{s}$



7 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

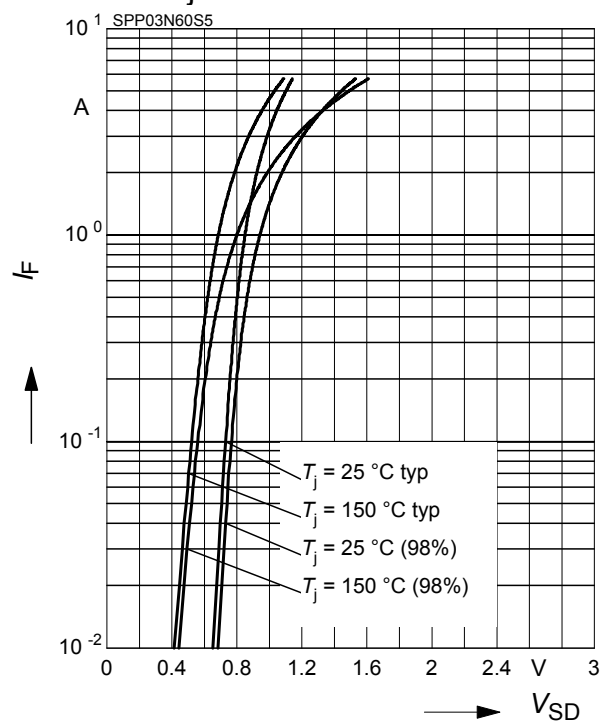
parameter: $I_D = 3.2 \text{ A pulsed}$



8 Forward characteristics of body diode

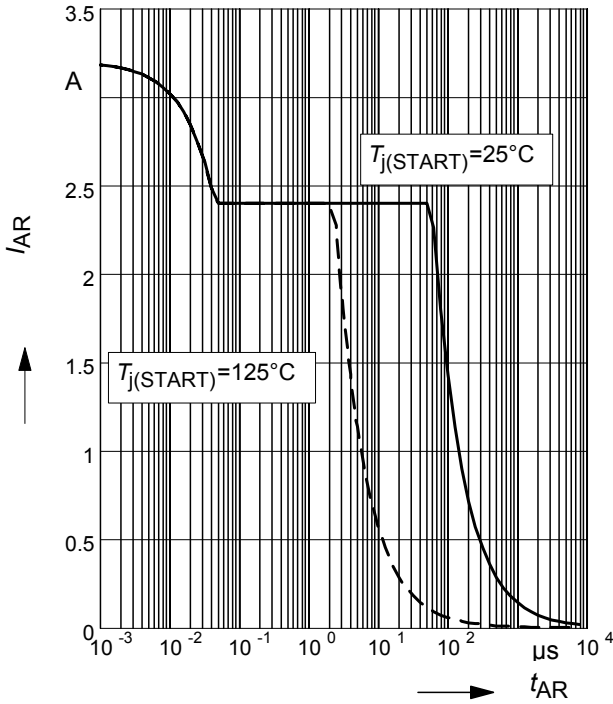
$$I_F = f(V_{SD})$$

parameter: T_j , $t_p = 10 \mu\text{s}$



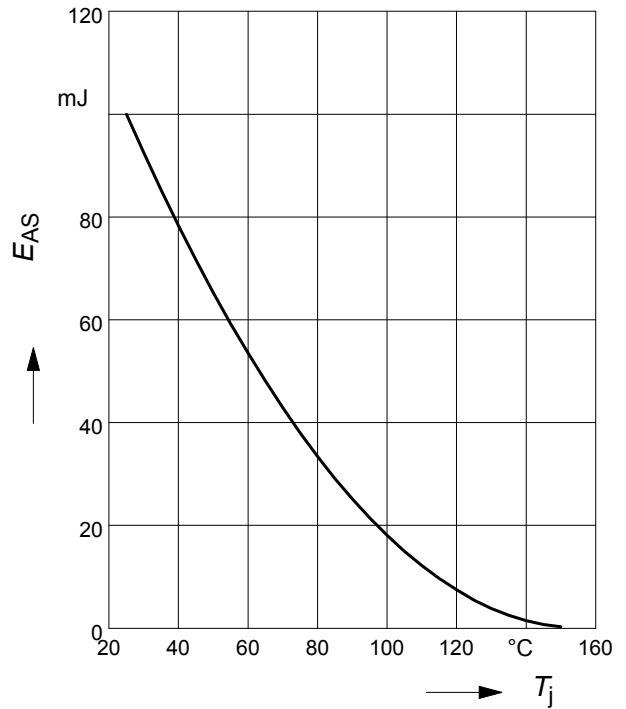
9 Avalanche SOA

$I_{AR} = f(t_{AR})$
 par.: $T_j \leq 150\text{ °C}$



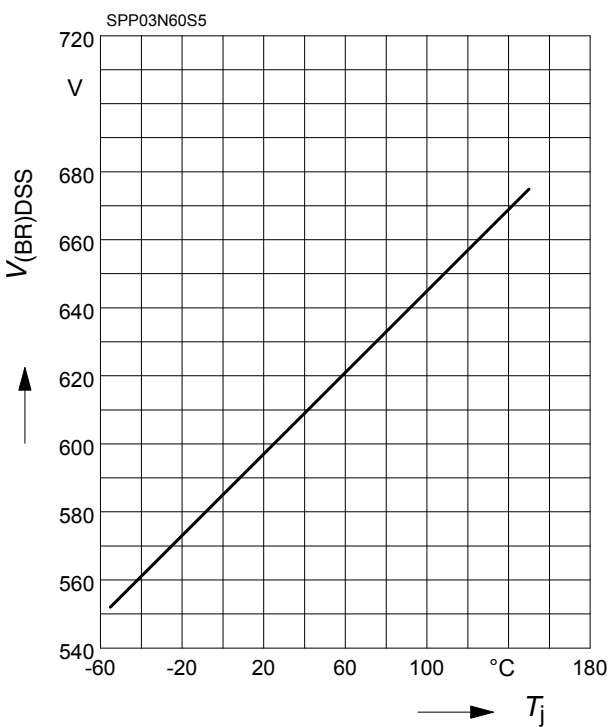
10 Avalanche energy

$E_{AS} = f(T_j)$
 par.: $I_D = 2.4\text{ A}$, $V_{DD} = 50\text{ V}$



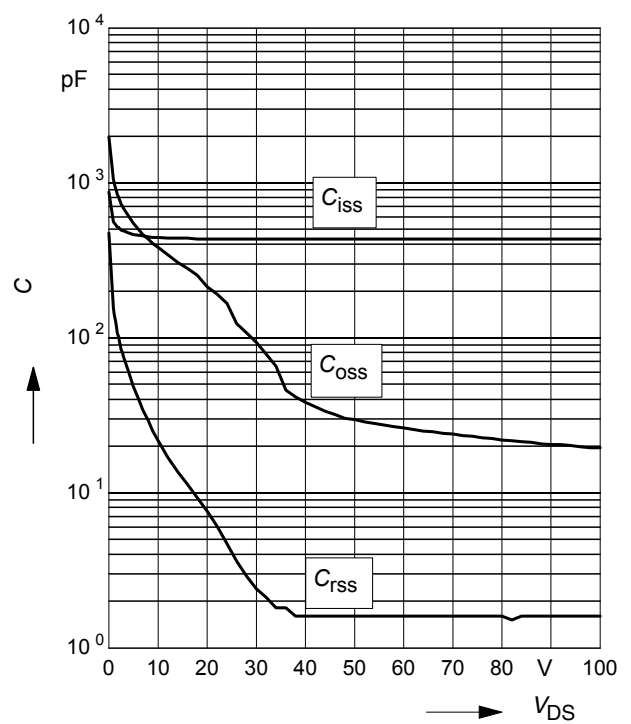
11 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$



12 Typ. capacitances

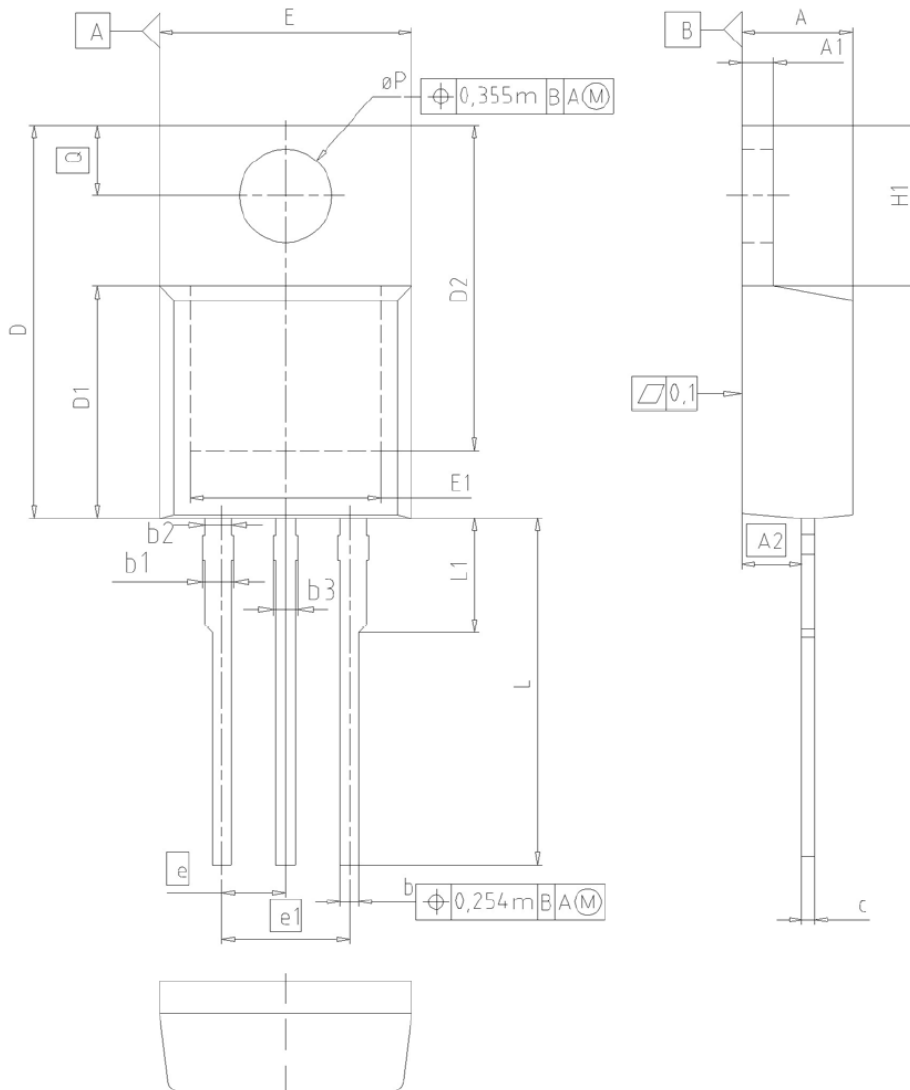
$C = f(V_{DS})$
 parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



Definition of diodes switching characteristics



PG-TO220-3-1, PG-TO220-3-21



| DIM | MILLIMETERS | | INCHES | |
|----------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| ϕP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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SCALE
0 2.5 5mm

EUROPEAN PROJECTION

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